

## General Description

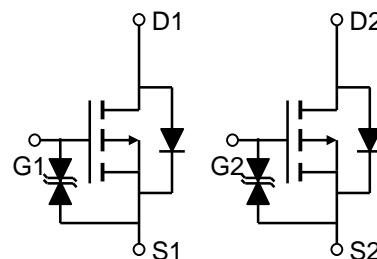
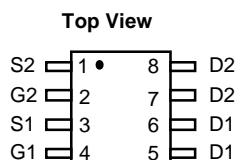
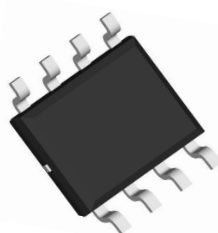
The AO4817 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications. The device is ESD protected.

## Features

$V_{DS}$  (V) = -30V  
 $I_D$  = -8A ( $V_{GS}$  = -20V)  
 $R_{DS(ON)}$  < 18m $\Omega$  ( $V_{GS}$  = -20V)  
 $R_{DS(ON)}$  < 21m $\Omega$  ( $V_{GS}$  = -10V)  
 ESD Rating: 1.5KV HBM



SOIC-8



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 25$	V
Continuous Drain Current <sup>A</sup>	$I_D$	-8	A
$T_A=25^\circ\text{C}$			
$T_A=70^\circ\text{C}$		-6.9	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-40	
Power Dissipation <sup>A</sup>	$P_D$	2	W
		$T_A=25^\circ\text{C}$	
$T_A=70^\circ\text{C}$		1.44	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	50	62.5	$^\circ\text{C/W}$
$t \leq 10\text{s}$				
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	73	110	$^\circ\text{C/W}$
Steady-State				
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	31	40	$^\circ\text{C/W}$

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
B <sub>V</sub> DSS	Drain-Source Breakdown Voltage	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-1 -5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±25V			±1	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250μA	-1	-2.8	-3	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-5V	-40			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-20V, I <sub>D</sub> =-8A T <sub>J</sub> =125°C		14.1	18	mΩ
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-8A		17.1	21	
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A		44		mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-8A		15		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V			-1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				-2.6	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz		1760	2200	pF
C <sub>oss</sub>	Output Capacitance			360		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			255		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		6.4	8	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-8A		30	38	nC
Q <sub>gs</sub>	Gate Source Charge			7		nC
Q <sub>gd</sub>	Gate Drain Charge			8		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>L</sub> =1.8Ω, R <sub>GEN</sub> =3Ω		12.5		ns
t <sub>r</sub>	Turn-On Rise Time			10.5		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			40		ns
t <sub>f</sub>	Turn-Off Fall Time			23		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-8A, dI/dt=100A/μs		24	30	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =-8A, dI/dt=100A/μs		16		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using <300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

Rev 3 : Nov. 2010

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

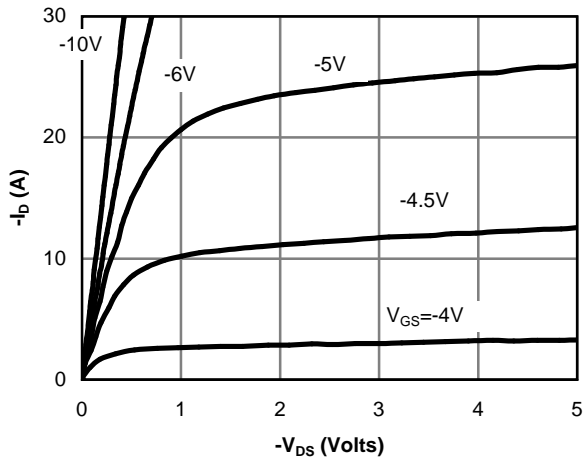


Fig 1: On-Region Characteristics

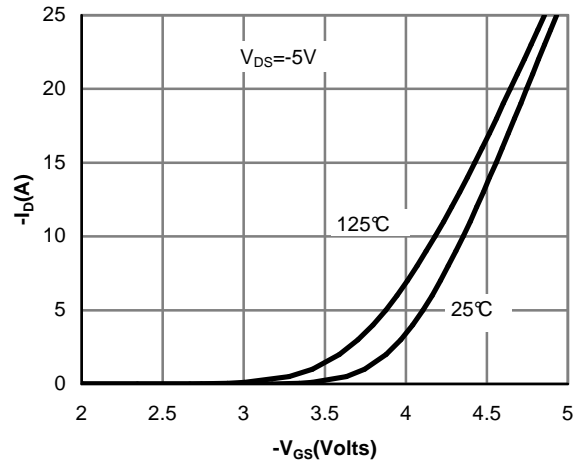


Figure 2: Transfer Characteristics

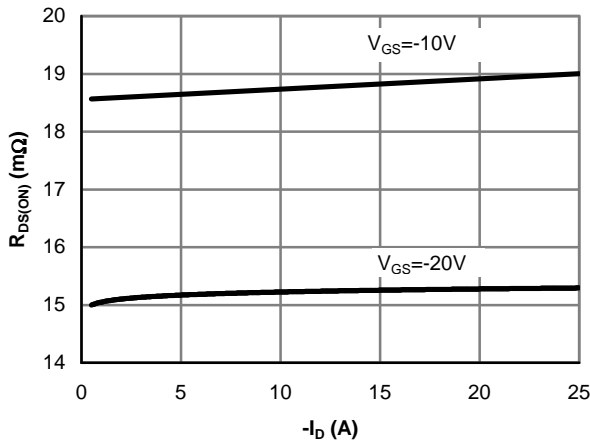


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

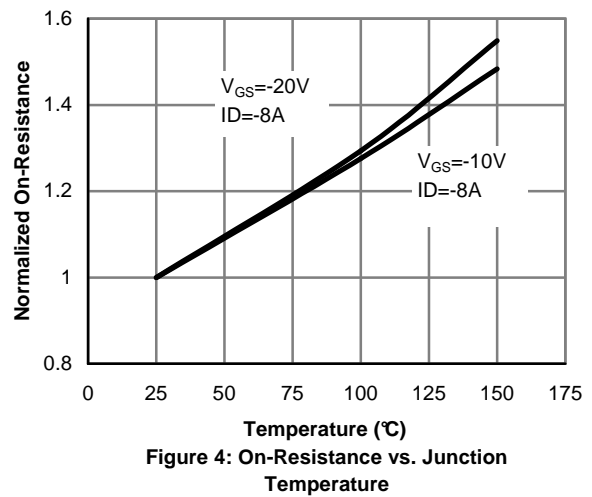


Figure 4: On-Resistance vs. Junction Temperature

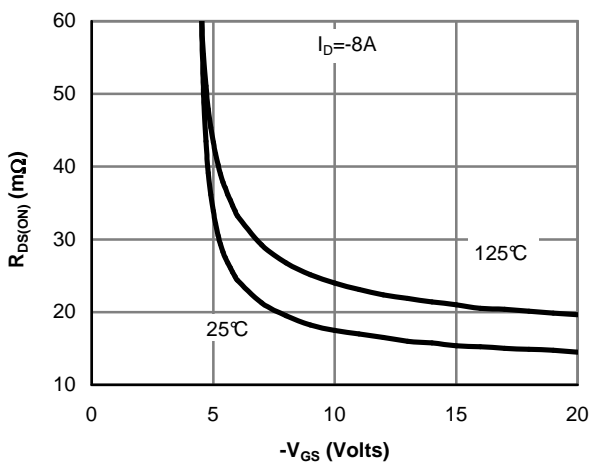


Figure 5: On-Resistance vs. Gate-Source Voltage

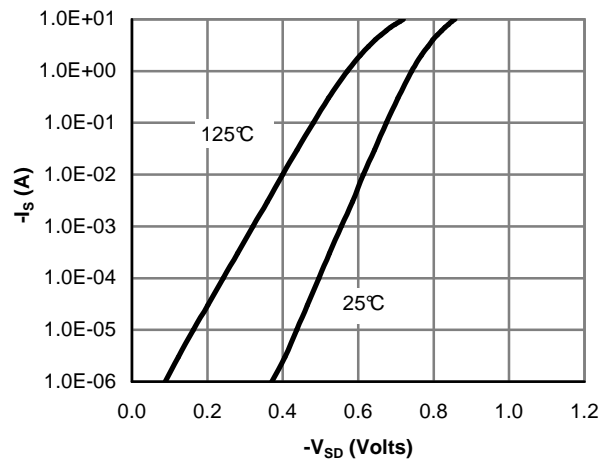
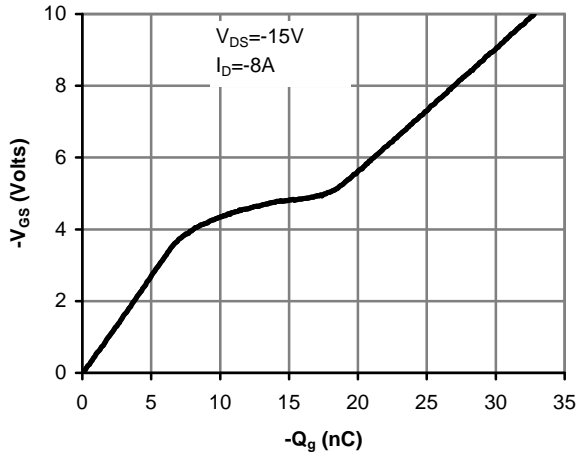
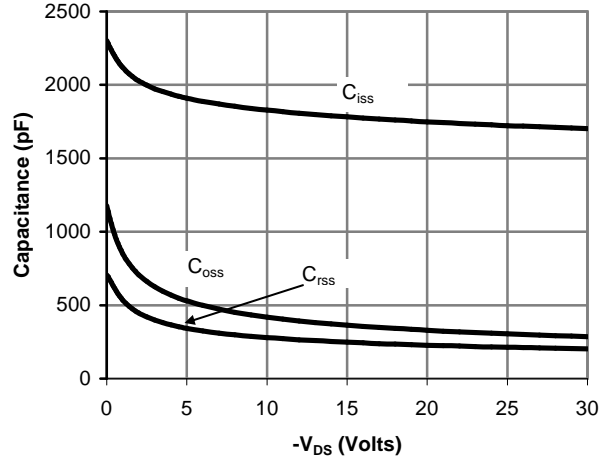


Figure 6: Body-Diode Characteristics

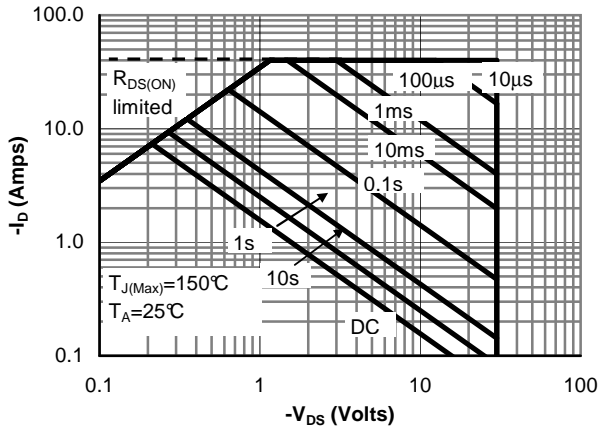
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



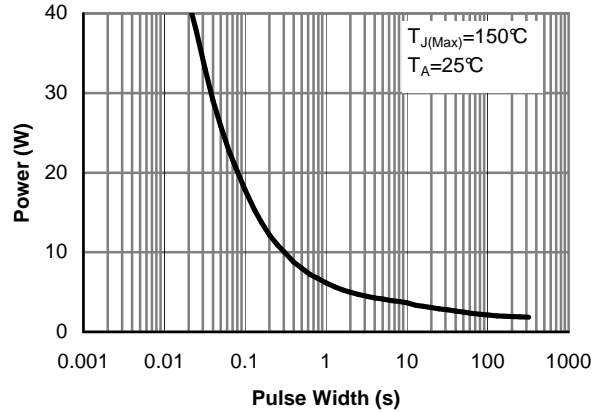
**Figure 7: Gate-Charge Characteristics**



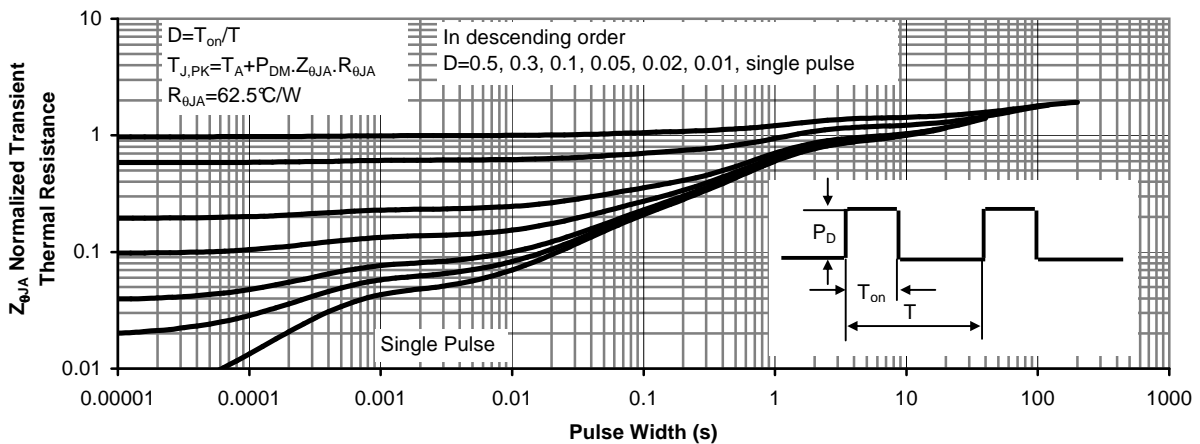
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area (Note E)**



**Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)**



**Figure 11: Normalized Maximum Transient Thermal Impedance**